AUTOMOTIVE

RoHS

COMPLIANT HALOGEN

FREE



### Vishay Semiconductors

# Hyperfast Rectifier, 3 A FRED Pt®



#### LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS				
I <sub>F(AV)</sub>	3 A			
$V_{R}$	100 V			
V <sub>F</sub> at I <sub>F</sub>	0.69 V			
t <sub>rr</sub>	25 ns			
T <sub>J</sub> max.	175 °C			
Package	SMC (DO-214AB)			
Circuit configuration	Single			

#### **FEATURES**

- Hyperfast recovery time, reduced Q<sub>rr</sub>, and soft recovery
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, piezo-injection, as high frequency rectifiers, and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

### **MECHANICAL DATA**

Case: SMC (DO-214AB)

Molding compound meets UL 94 V-0 flammability rating **Terminals:** matte tin plated leads, solderable per

J-STD-002

Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage	$V_{RRM}$		100	V
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>Sp</sub> = 142 °C	3	۸
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C, 6 ms square pulse	130	А
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	$V_{BR}, V_{R}$	$I_R = 100  \mu A$	100	-	-	
Forward voltage, per diode V <sub>F</sub>		I <sub>F</sub> = 3 A	-	0.83	0.90	V
	٧F	I <sub>F</sub> = 3 A, T <sub>J</sub> = 125 °C	-	0.69	0.75	
Reverse leakage current, per diode		$V_R = V_R$ rated		-	2	
Reverse leakage current, per diode		T <sub>J</sub> = 125 °C, V <sub>R</sub> = V <sub>R</sub> rated	-	1	10	μA
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 100 V	-	23	-	pF



# Vishay Semiconductors

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1 A, dI_F/dt = 50$	A/ $\mu$ s, $V_R = 30 \text{ V}$	-	27	-	
Payaraa raaayar tima		I <sub>F</sub> = 0.5 A, I <sub>R</sub> = 1 A, I <sub>rr</sub> = 0.25 A		-	-	25	
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 3 A,	-	18	-	ns
		T <sub>J</sub> = 125 °C		-	30	-	
Peak recovery current I <sub>RRM</sub>	1	T <sub>J</sub> = 25 °C		-	2.1	-	A
	T <sub>J</sub> = 125 °C	$dI_F/dt = 200 A/\mu s,$ $V_R = 100 V$	-	4	-	A	
Reverse recovery charge Q <sub>rr</sub>	0	T <sub>J</sub> = 25 °C	*H = 100 *	-	19	-	nC
	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	60	-	iiC

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C
Thermal resistance, junction to mount	R <sub>thJM</sub>	Device mounted on PCB with 2 x 3.5 mm soldering lands	-	7.7	14	°C/W
Approximate weight				0.24		g
Approximate weight			·	0.008		oz.
Marking device		Case style SMC (DO-214AB)		31	<del>-</del> 11	

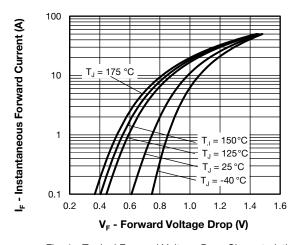


Fig. 1 - Typical Forward Voltage Drop Characteristics

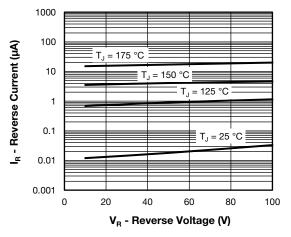


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



### www.vishay.com

## Vishay Semiconductors

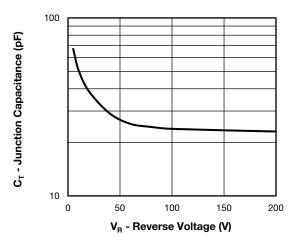


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

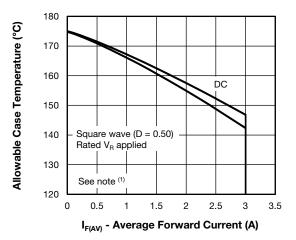


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

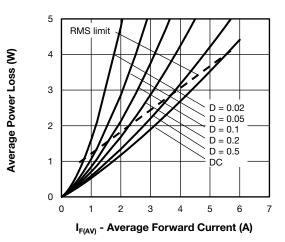


Fig. 5 - Forward Power Loss Characteristics

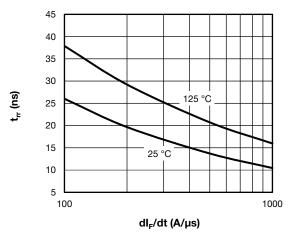


Fig. 6 - Typical Reverse Recovery Time vs.  $dI_F/dt$ 

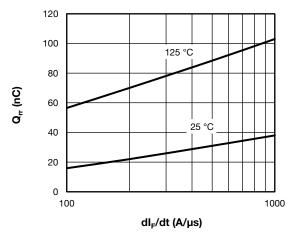
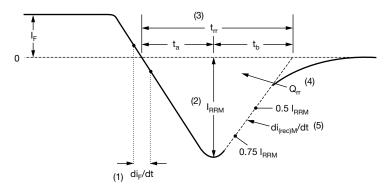


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

### Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 5)}; \\ Pd_{REV} = \text{inverse power loss} = V_{R1} \times I_R \text{ (1 - D); } I_R \text{ at } V_{R1} = \text{rated } V_R \\ \end{array}$ 

## Vishay Semiconductors

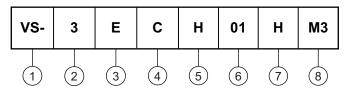


- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (4)  ${\rm Q_{rr}}$  area under curve defined by  ${\rm t_{rr}}$  and  ${\rm I_{RRM}}$
- (2)  $I_{RRM}$  peak reverse recovery current
- $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.
- (5) di<sub>(rec)M</sub>/dt peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 8 - Reverse Recovery Waveform and Definitions

### **ORDERING INFORMATION TABLE**

### Device code



- Vishay Semiconductors product
- 2 Current code (3 = 3 A)
- 3 Circuit configuration:

E = single diode

- C = SMC package
- 5 Process type,

H = hyperfast recovery

- 6 Voltage code (01 = 100 V)
- 7 H = AEC-Q101 qualified
- M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-3ECH01HM3/9AT	3500	3500	13"diameter plastic tape and reel			

LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?95402</u>				
Part marking information	www.vishay.com/doc?95472			
Packaging information	www.vishay.com/doc?95404			



# Vishay Semiconductors

## **SMC**

### **DIMENSIONS** in inches (millimeters)

### **DO-214AB (SMC)**



### **Mounting Pad Layout**





### **Legal Disclaimer Notice**

Vishay

### **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.